## ACIS Gain Challenges

## Warm Focal Plane Temperatures <br> \& <br> Lorentzians

1. ACIS Gain Challenges

Cause of Gain decline.
How Chandra ACIS detector time-dependent gain is calibrated.
Calibration Challenges \& Solutions.
2. ACIS Warm Focal Plane Temperature Calibration

Analyses of 2017-2018 ECS observations of Al-Ka, Ti-Ka, Mn-K lines.
Lorentzian vs. Gaussian natural line emission profile.
FWHM vs FP_TEMP

## Charge Transfer Inefficiency

ACIS CCD architecture



1) Charge Loss

2) Grade Migration


CTI manifests two modes:

1) Gain decline

Charge loss: Portion of charge packet is trapped, reducing overall PHA
2) QE decline

Grade migration: Trapped event charge is re-emitted into a trailing event island pixel during readout.

## How ACIS Gain is Calibrated

## External Calibration Source (ECS)

ACIS exposed when HRC is in the focal plane Fe55 sources, $\mathrm{T}_{1 / 2}=2.7$ years Bright ECS lines:

| Al-K $\alpha$ | 1.49 keV |
| :--- | :--- |
| Ti-K | 4.51 keV |
| $\mathrm{Mn}-\mathrm{K} \mathrm{\alpha}$ | 5.89 keV |



## Line Energy Centroid Fit PHA Channel Spectrum

Simple Calculation to find Line Centroids
Fit at each $32 \times 32$ pixel location across the ACIS CCDs


PHA channel space histogram
NO gain correction applied during data reprocessing
1 channel $\approx 4.5 \mathrm{eV}$

## Line Energy Centroid Fit vs ChipY



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## Line Energy Centroid Fit vs ChipY



## dPHA vs ChipY

Gain correction $=\mathrm{dPHA}[\mathrm{x}, \mathrm{y}, \mathrm{E}]$
Each location fit AI, Ti, Mn dPHA to energy scaling equation:

$$
d P H A=A \sqrt{E}+B E
$$

Solve for "A" and "B" coefficients. Unique for each chip( $x, y$ ) location.


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s3 e20

## ECS Evolution



## ECS Evolution



## ECS Evolution



## ECS Evolution

```
6 \text { months of ECS}
64\times64 pixel regions
\(=8 x\) more counts
```


## ACIS-S3 Epoch75+76 8/1/2018-1/31/2019



## No More Simple Line Centroid Fitting

Physical model does not exist.
Approximate the expected line profile using the shape of the response.

1. Extract RESPONSE vs PHA_Channel from RMF.
@ Energy corresponding to nominal Al-Ka, Ti-Ka, Mn-Ka
*(DET_GAIN Calibration Required for keV -to- PHA_Channel conversion)
@ Each spatial fitting region
$32 \times 32$ pixels $\quad$ I0/1/2/3, S2/3
$64 \times 64$ pixels S1
256x32 pixels S0/4/5
2. Fit multiple gaussians to the response.
3. Stitch together the Model =

GAUSS_1 LineE thawed
GAUSS_1 norm thawed
GAUSS_1 sigma thawed
Subsequent gaussians LineE tied to GAUSS_1
*(offset relative to GAUSS_1)
Subsequent gaussians norm tied to GAUSS_1
Subsequent gaussians sigma tied to GAUSS_1
*Revised to 64x64 for TGAIN 3.0


## 1. Line Energy Fitting Constraints

- PHA channel search windows relative to RMF PHA channel peak (includes DET_GAIN correction to PHA) calculated from nominal Al-Ka, Ti-Ka, and Mn-Ka line energies.
- Search windows tailored to expectations:

10 and 12 windows RMF_PK-100 < PHA Search Window < RMF_PK+80
All other chips RMF_PK-100 < PHA Search Window < RMF_PK+15
FI chip node1/2 boundary region extends lower search channel to RMF_PK-120

- Initial line centroids = mean(channel @ 90\% max counts), weighted by smoothed counts.
- Abort fit if total counts within response FWHM < 6 (Al, Ti), or < 8 (Mn).
- Fit multiple-gaussian model to each Al, Ti, Mn line.

Al model:
multiple gaussian, fixed to $1^{\text {st }}$ gaussian
peak counts lower limit = 1.75
sigma lower limit = response sigma
initial_LineE - 15 > LineE > initial_LineE + 15

+ mean_background
+ multiple gaussian model of Si-Ka, frozen to: sigma= Al-K sigma, norm= max(smoothed counts within Si-Ka
window), LineE= channel @ max_counts within Al-K人 initial centroid x [1.14, 1.2]
Ti/Mn models similar to above, $\mathrm{K} \beta$ components replace Si-K $\quad$ model.


## 2. Time-Dependent Gain Correction Fitting

- lowess, error weighted, smoothing LineE vs ChipY, for each ChipX column

Smoothing factor relaxed at FI node1/2 boundary
Missing data (LineE fitting did not converge) replaced with linear interpolation to nearby values

- Fit each ChipY set of dPHA values to energy scaling equation.

$$
d P H A=A \sqrt{E}+B E
$$

"A" and "B" coefficients thawed for all chips, "B" coefficient limited to: $1<B<8$
dPHA values for each line are weighted based on total line counts: Ti-K $<\mathrm{Al}-\mathrm{Ka}<\mathrm{Mn}-\mathrm{Ka}$

- Limit "B" coefficient for the column, and smooth versus ChipY:
mean(B) - stdev(B) < "B" < mean (B) + stdev(B)
lowess smooth "B", error weighting = reverse(chipY)
- Fit again with "B" coefficient frozen.



## I3 LineE Before / After TGAIN Correction

Epoch 20
I3
Chip $X=1: 32$

chip Y midpoint

chip $Y$ midpoint

## I3 LineE Before / After TGAIN Correction

Epoch 20
I3
Chip $X=1: 32$

chipY midpoint

chip $Y$ midpoint

## Most Recent TGAIN Correction

 S3 $x=1: 64$s3 ciao4.11_caldb4.8.2_120_v3_64x64y
s3 ciao4.11_cald64.8.2_120_v3_64x64y

PHA channel




## Intermission...



## ACIS Warm Focal Plane Temperature Effects on Data Quality

## Data

Epochs 70-75
1.5 years

5/1/2017-10/31/2018
128x 128y pixel regions
aimpoint chips

| I3 |  |
| :--- | :--- |
| FP_TEMP | ksec |
| $-120:-119$ | 600 |
| $-119:-118$ | 178 |
| $-118:-117$ | 141 |
| $-117:-116$ | 168 |
| $-116:-115$ | 161 |
| $-115:-114$ | 219 |
| $-114:-113$ | 199 |
| $-113:-112$ | 112 |
| $-112:-111$ | 69 |
| $-109:-108$ | 94 |


| S3 |  |
| :--- | :--- |
| FP_TEMP | ksec |
| $-120:-119$ | 842 |
| $-119:-118$ | 265 |
| $-118:-117$ | 223 |
| $-117:-116$ | 243 |
| $-116:-115$ | 244 |
| $-115:-114$ | 291 |
| $-114:-113$ | 267 |
| $-113:-112$ | 172 |
| $-112:-111$ | 103 |
| $-109:-108$ | 94 |

## ECS Model

$K \alpha_{1,2}$ and $K \beta_{1,3}$ x-ray emission lines of the $3 d$ transition metals

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> (Received 14 May 1997)

PI Channel Space, DETGAIN \& TGAIN Corrected

Al fit window= $\quad 0.9-2.1 \mathrm{keV}$
Ti \& Mn fit window= 3.3-7.2 keV

ECS LINES
Al-Ka lorentzian
Al-Kb lorentzian
Ti-Ka1
Ti-Ka2
Ti-Kb
Mn-Ka
Mn-Kb lorentzian lorentzians

FREE: norm, width=initial scaled to chipY, LineE norm=tied*Al-Ka, width=Al-Ka, LineE=tied*Al-Ka FREE: norm, width=initial scaled to chipY, LineE norm=tied*Ti-Ka1, width=Ti-Ka1, LineE=tied*Ti-Ka1 norm=FREE, width=Ti-Ka1, LineE=FREE
FREE: norm, width=initial scaled to chipY, LineE +6 additional lorentzians norm=FREE, width=Mn-Ka, LineE=FREE
+4 additional lorentzians norm=tied, width=lorentz_0, LineE=tied

INSTRUMENTAL

| Si-Ka | gaussian | fixed \& chipY scaled for I-array |
| :--- | :--- | :--- |
| Au-Ma1 | gaussian | fixed \& chipY scaled |
| Au-Ma2 | gaussian | tied to Au-Ma1 |
| Au-Mb | gaussian | tied to Au-Ma1 |
| Au-Mg | gaussian | tied to Au-Ma1 |
| Ni-Ka | gaussian | fixed |
| Au-La | gaussian | fixed |
| framestore $A u-M$ | gaussian | fixed \& chipY scaled |
| framestore | Ni-Ka | gaussian |

BACKGROUND Continuum, empirical model for 0.85-7.2 keV for I-array
powlaw low energy component, Pholndex>0
powlaw high energy component, Pholndex<0
gaussian $\quad 0.85>E>1.0$ low energy addition

$$
\operatorname{Gauss}(E)=K \frac{1}{\sigma \sqrt{2 \pi}} \exp \frac{-\left(E-E_{0}\right)^{2}}{2 \sigma^{2}}
$$

## Lorentz vs Gauss S3 Ti \& Mn

GAUSS


LORENTZ

FWHM ACIS-S3


FWHM ACIS-I3


